

December 2009

FJN3303F High Voltage Fast-Switching NPN Power Transistor

Features

- · High Voltage Capability
- High Switching Speed
- · Suitable for Electronic Ballast and Charger
- · Green packaging



Absolute Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units				
V _{CBO}	Collector-Base Voltage	700	V				
V _{CEO}	Collector-Emitter Voltage	400	V				
V _{EBO}	Emitter-Base Voltage	9	V				
I _C	Collector Current (DC)	1.5 A					
I _{CP}	Collector Current (Pulse) *	3	А				
I _B	Base Current (DC)	0.75	А				
I _{BP}	Base Current (Pulse) *	1.5	А				
TJ	Junction Temperature	150	°C				
T _{STG}	Storage Temperature range	-65 to +150	°C				

^{*} Pulse Test: Pulse Width = 5ms, Duty Cycle ≤ 10%

Thermal Characteristics $T_A = 25$ °C unless otherwise noted

Symbol	Parameter		Value	Units
P _D	Total Device Dissipation	T _C = 25°C T _A = 25°C	1.1 650	W mW
$R_{\theta JC}$	Thermal Resistance Junction-Case	е	48	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Amb	ient	190	°C/W

Ordering Information

Part Number	Marking Info.	Package	Packing Method	Remarks
FJN3303FBU	J3303F	TO-92 (Straight)	BULK	Green EMC
FJN3303FTA	J3303F	TO-92 (Form)	AMMO	Green EMC

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FJN3303F Rev. A1

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Electrical Characteristics $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	700			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	9			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 700V, I_{E} = 0$			10	μА
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			10	μА
h _{FE1}	DC Current Gain	$V_{CE} = 2V, I_{C} = 0.5A$ $V_{CE} = 2V, I_{C} = 1.0A$	14 5		23	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$ $I_C = 1.5A, I_B = 0.5A$			0.5 1.0 3.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 0.5A, I_B = 0.1A$ $I_C = 1.0A, I_B = 0.25A$			1.0 1.2	V V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.1A$	4			MHz
t _{ON}	Turn On Time	V _{CC} = 125V, I _C = 1A			1.1	μS
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = -0.2A$			4.0	μS
t _F	Fall Time	$R_L = 125\Omega$			0.7	μS

Typical Performance Characteristics

Figure 1. Static Characteristic

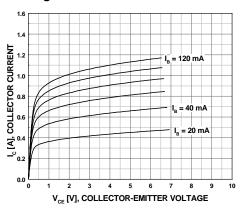


Figure 2. DC Current Gain

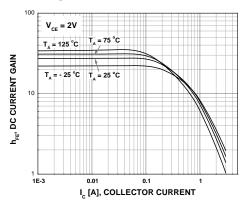


Figure 3. Collector-Emitter Saturation Voltage

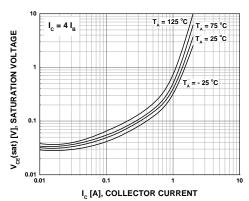


Figure 4. Base-Emitter Saturation Voltage

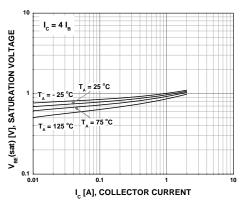


Figure 5. Resistive Load Switching Time

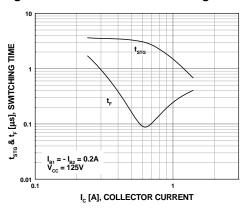
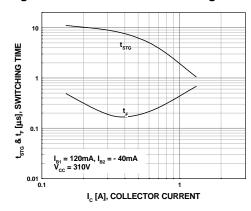


Figure 6. Resistive Load Switching Time



Typical Performance Characteristics (Continued)

Figure 7. Forward Biased Safe Operating Area

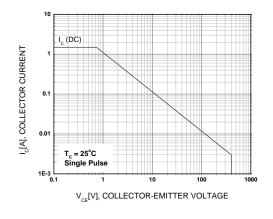


Figure 8. Reverse Biased Safe Operating Area

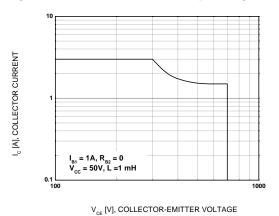
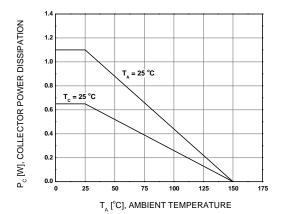


Figure 9. Power Derating

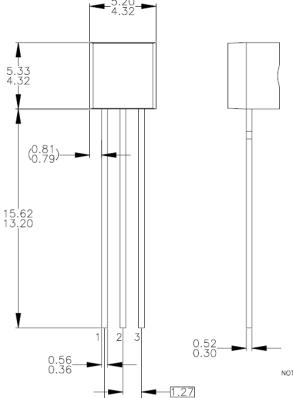


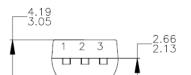
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Physical Dimension

TO-92 (STD Straight Lead)





2.54

NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
 ALL DIMENSIONS ARE IN MILLIMETERS.
 DRAWING CONFORMS TO ASME Y14.5M-1994.
 TO-92 (92.94.96.97.98) PIN CONFIGURATION:

D)	10-	92	(92	,94,	90,	97,5	10)	I-IIA	CC	JINIT	GUP	MIII	JIN:				
						96									98		
		_	_		-	_		-	_		-	_					

z		92			94		96			97			98		
₫	Р	F	М	Р	F	М	Р	F	М	Ρ	F	М	Р	F	М
1	Ε	S	S	Ε	S	S	В	D	G	C	G	D	C	G	D
2	В	D	G	C	G	D	Ε	S	S	В	D	G	Ε	S	S
3	С	G	D	В	D	G	С	G	D	Ε	S	S	В	D	G

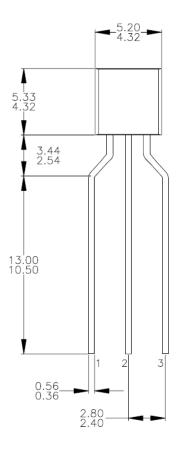
LEGEND: P - BIPOLAR F - JFET M - DMOS EMITTERBASECOLLECTOR

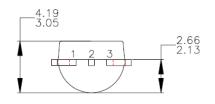
- E) FOR PACKAGE 92, 94, 96, 97 AND 98:
 PIN CONFIGURATION DRAIN "D" AND SOURCE "S"
 ARE INTERCHANGEAGLE AT JFET "F" OPTION.
 F) DRAWING FILENAME: MKT-ZAO3DREV3.

Dimensions in Millimeters

Physical Dimension (Continued)

TO-92 (Lead Form_J61Z)







NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
 ALL DIMENSIONS ARE IN MILLIMETERS.
 DRAWING CONFORMS TO ASME Y14.5M-1994,
 TO-92 (92,94,96,97,98) PIN CONFIGURATION:

z		92			94			96			97			98	
□	Р	F	М	Р	F	М	Ρ	F	М	Р	F	М	Р	F	М
1	Ε	S	S	Ε	S	S	В	D	G	С	G	D	С	G	D
2	В	D	G	C	G	D	Ε	S	S	В	D	G	Ε	S	S
3	С	G	D	В	D	G	С	G	D	Ε	S	S	В	D	G

LEGEND: P - BIPOLAR F - JFET M - DMOS E - EMITTER B - BASE C - COLLECTOR D - DRAIN S - SOURCE G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98:
 PIN CONFIGURATION DRAIN "D" AND SOURCE "S"
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 F) DRAWING FILENAME: MKT-ZAO3FREVZ.

Dimensions in Millimeters



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Rev. I41